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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
. 10/544,253	08/02/2005	Yoshiaki Ohbayashi	0388-051646	1352	
28289 THF WFRR I	28289 7590 03/30/2007 THE WEBB LAW FIRM, P.C.			EXAMINER	
700 KOPPERS BUILDING			LE, HUYEN D		
436 SEVENTH AVENUE PITTSBURGH, PA 15219		•	ART UNIT	PAPER NUMBER	
•			2615		
					
SHORTENED STATUTOR	RY PERIOD OF RESPONSE	MAIL DATE	DELIVERY MODE		
3 MONTHS		03/30/2007	PAPER		

Please find below and/or attached an Office communication concerning this application or proceeding.

If NO period for reply is specified above, the maximum statutory period will apply and will expire 6 MONTHS from the mailing date of this communication.

	Application No.	Applicant(s)				
055 - 4-41 0	10/544,253	OHBAYASHI ET AL.				
Office Action Summary	Examiner	Art Unit				
	HUYEN D. LE	2615				
The MAILING DATE of this comm Period for Reply	unication appears on the cover sheet	with the correspondence address				
A SHORTENED STATUTORY PERIOD WHICHEVER IS LONGER, FROM THE - Extensions of time may be available under the provisi after SIX (6) MONTHS from the mailing date of this cc - If NO period for reply is specified above, the maximum - Failure to reply within the set or extended period for re - Any reply received by the Office later than three montly earned patent term adjustment. See 37 CFR 1.704(b)	MAILING DATE OF THIS COMMUN ons of 37 CFR 1.136(a). In no event, however, may ommunication. In statutory period will apply and will expire SIX (6) Mo eply will, by statute, cause the application to become this after the mailing date of this communication, even	NICATION. a reply be timely filed ONTHS from the mailing date of this communication. ABANDONED (35 U.S.C. § 133).				
Status						
1) Responsive to communication(s)	filed on 02 August 2005.					
2a)☐ This action is FINAL .	2b)⊠ This action is non-final.					
/ —	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is					
closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Disposition of Claims						
4)⊠ Claim(s) 10-18 is/are pending in t	4)⊠ Claim(s) <u>10-18</u> is/are pending in the application.					
	4a) Of the above claim(s) is/are withdrawn from consideration.					
5) Claim(s) is/are allowed.						
6)⊠ Claim(s) <u>10-18</u> is/are rejected.						
7) Claim(s) is/are objected to	· · · ——					
8) Claim(s) are subject to res	triction and/or election requirement.					
Application Papers						
9)☐ The specification is objected to by	the Examiner.					
10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.						
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
• • • • • • • • • • • • • • • • • • • •		ng(s) is objected to. See 37 CFR 1.121(d).				
11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.						
Priority under 35 U.S.C. § 119						
12)⊠ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a)⊠ All b)☐ Some * c)☐ None of:						
1. Certified copies of the priority documents have been received.						
2. Certified copies of the priority documents have been received in Application No						
3. Copies of the certified copies of the priority documents have been received in this National Stage						
• •	tional Bureau (PCT Rule 17.2(a)).					
* See the attached detailed Office ac	tion for a list of the certified copies no	ot received.				
Attachment(s)						
1) Notice of References Cited (PTO-892) 4) Interview Summary (PTO-413) Notice of Draftsperson's Patent Drawing Review (PTO-948) Paper No(s)/Mail Date						
3) Information Disclosure Statement(s) (PTO/SB/0 Paper No(s)/Mail Date 10/2/06&7/5/06.		f Informal Patent Application				

DETAILED ACTION

Specification

1. The disclosure is objected to because of the following informalities: the term "SOI" needs to be described in the specification.

Appropriate correction is required.

Claim Objections

2. Claims 13, 14 and 16-17 are objected to because of the following: the term single crystal silicon on insulator needs to be inserted before "SOI". Appropriate correction is required.

Claim Rejections - 35 USC § 103

- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

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4. Claims 10-18 are rejected under 35 U.S.C. 103(a) as being unpatentable over Bernstein (U.S. patent 5,452,268).

Regarding claim 10, Bernstein'268 teaches an acoustic transducer that comprises a back electrode (12) forming perforations (13) therein corresponding to acoustic holes and a diaphragm (16). As shown in figure 1, the diaphragm (16) is mounted on a substrate (the silicon substrate 18) while the back electrode (12) is mounted in a position opposed to the diaphragm across a void as claimed. The back electrode (12) is formed by polycrystal silicon (col. 2, lines 57-62, col. 3, lines 25-30).

Bernstein does not specifically teach a thickness as claimed. However, Bernstein does not limit to any thickness for the back electrode.

Therefore, it would have been obvious to one skilled in the art to provide any thickness for the back electrode (12) of Bernstein such as the thickness of 5 microns to 20 microns depending on the applications and the desired frequency characteristics.

Regarding claim 11, Bernstein does not specifically teach that the substrate (18) is a monocrystal silicon substrate. However, it is known in the art to provide monocrystal silicon for the substrate in the capacitive acoustic transducers.

Therefore, it would have been obvious to one skilled in the art to provide monocrystal silicon for the substrate (18) for an alternate choice.

Regarding claim 12, Bernstein teaches an impurity diffusion treatment that is executed on the diaphragm (col. 4, lines 42-48).

Regarding claims 13-15, Bernstein teaches the substrate (18) that comprises a support substrate having a silicon substrate and consisting of the single crystal silicon on insulator (SOI)

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wafer as claimed (figure 1). The SOI wafer has an active layer used as a diaphragm (16) of monocrystal silicon (col. 2, lines 57-62, col. 3, lines 25-30).

Bernstein does not specifically teach a thickness as claimed in claim 15. However, Bernstein does not limit to any thickness for the diaphragm.

Therefore, it would have been obvious to one skilled in the art to provide any thickness for the diaphragm (16) of Bernstein such as the thickness of 0.5 to 5 microns depending on the applications and the desired frequency characteristics.

Regarding claims 16-17, Bernstein shows the SOI structure that includes a silicon oxide film (14, col. 3, lines 63-64) formed on a monocrystal silicon substrate (18), and a polycrystal silicon film (16, col. 3, lines 25-30 and col. 5, lines 1-7) formed on the silicon oxide film (14).

Regarding claims 18, Bernstein teaches the diaphragm (16) that is formed of polycrystal silicon (col. 2, lines 57-62, col. 3, lines 25-30 and col. 5, lines 1-7).

Bernstein does not specifically teach a thickness as claimed in claim 18. However, Bernstein does not limit to any thickness for the diaphragm.

Therefore, it would have been obvious to one skilled in the art to provide any thickness for the diaphragm (16) of Bernstein such as the thickness of 0.5 to 5 microns depending on the applications and the desired frequency characteristics.

Conclusion

5. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

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Bernstein (U.S. patent 5,146,435) teaches a construction of a capacitor acoustic transducer.

Ling (U.S. patent 5,208,789) teaches a construction of a condenser microphone.

6. Any inquiry concerning this communication or earlier communications from the

examiner should be directed to HUYEN D. LE whose telephone number is (571) 272-7502. The

examiner can normally be reached on 9:30AM-6:00PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, SINH TRAN can be reached on (571) 272-7564. The fax phone number for the

organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

applications is available through Private PAIR only. For more information about the PAIR

system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would

like assistance from a USPTO Customer Service Representative or access to the automated

information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

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March 27, 2007

PRIMARY EXAMINER